Abstracts

A high-performance GaAs SP3T switch for digital cellular systems

Zeji Gu, Shuyun Zhang, D. Johnson, S. Belletete, M. Ayvazian and D. Fryklund. "A high-performance GaAs SP3T switch for digital cellular systems." 2001 MTT-S International Microwave Symposium Digest 01.1 (2001 Vol. I [MWSYM]): 241-244 vol.1.

A high-performance GaAs SP3T switch has been developed using asymmetrical design of the transmit and receive paths. A combination of stacked FETs and multi-gate PHEMT FETs with high breakdown voltages and large peripheries was implemented in this design. Insertion loss of less than 0.8 dB and isolation greater than 25 dB to 2 GHz were obtained. With a positive 3-V control voltage, power handling of the device exceeded 34 dBm while maintaining second and third harmonic levels better than 65 dBc.

❑ Return to main document.